

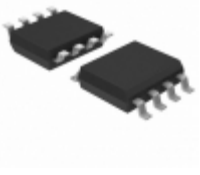
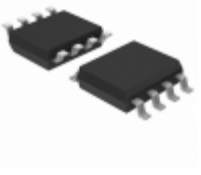





	<h2>SI4104DY-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI4104DY-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 100V 4.6A 8-SOIC</p> <p>Datenblätter:  SI4104DY-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 10123 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI4104DY-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 100V 4.6A 8-SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	10123 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SO
Verlustleistung (max)	2.5W (Ta), 5W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	4.6A (Tc)
Rds On (Max) @ Id, Vgs	105 mOhm @ 5A, 10V
VGS (th) (Max) @ Id	4.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	13nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	446pF @ 50V
Verpackung	Tape & Reel (TR)



















































SI4104DY-T1-GE3 ist neu im Original, Suche SI4104DY-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4104DY-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI4104DY-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI4108DY Vishay Precision Group SI4108DY VISHAY</p>	 <p>SI4104DY-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 4.6A 8-SOIC</p>	 <p>SI4104DY-T1-E3 Vishay / Siliconix MOSFET N-CH 100V 4.6A 8-SOIC</p>	 <p>SI4108DY-T1-GE3 Vishay / Siliconix MOSFET N-CH 75V 20.5A 8-SOIC</p>
 <p>SI4104DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 4.6A 8-SOIC</p>	 <p>SI4108DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 75V 20.5A 8-SOIC</p>	 <p>SI4110DY-T1-E3 Vishay Precision Group SI4110DY-T1-E3 VISHAY</p>	 <p>SI4102DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 3.8A 8-SOIC</p>

heiße Teile

Mehr

 SI4012-C1001GTR	 SI4021-A1-FTR	 SI4022-A0-FTR	 SI4022-A1-FTR	 SI4030-A0-FM
 SI4032-V2-FMR	 SI4033-B2-FM	 SI4048DY-T1-E3	 SI4056DY	 SI4056DY-T1-E3
 SI4056SPG	 SI4058DY	 SI4090DY	 SI4100BDDY-T1-GE3	 SI4100DY
 SI4100DY-T1-E3	 SI4100DY-T1-E3	 SI4100DY-T1-GE3	 SI4100DY-T1-GE3	 SI4102DY
 SI4102DY-T1-E3	 SI4102DY-T1-E3	 SI4102DY-T1-GE3	 SI4102DY-T1-GE3	 SI4104DY-T1-GE3
 SI4108DY-T1-GE3	 SI4108DY-T1-GE3	 SI4110DY-T1-GE3	 SI4110DY-T1-GE3	 SI4112-D-GM
 SI4113-BMR	 SI4114DY	 SI4114DY-T1-E3	 SI4114DY-T1-E3	 SI4114DY-T1-GE3
 SI4114DY-T1-GE3	 SI4116DY	 SI4116DY-T1-E3	 SI4116DY-T1-E3	 SI4116DY-T1-GE3
 SI4116DY-T1-GE3	 SI4122-BTR	 SI4122-D-GMR	 SI4122DY-T1-E3	 SI4122G-BMR
 SI4123-BM	 SI4124DY-T1-E3	 SI4124DY-T1-E3	 SI4124DY-T1-GE3	 SI4124DY-T1-GE3

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